

Attorney Docket No. 08038.0027
Serial No. 09/658,861

forming a second insulating layer comprising silicon, carbon and nitrogen on said first insulating layer;

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selectively etching said second insulating layer until the surface of said first insulating layer is partially exposed,

selectively etching said first insulating layer with plasma, using said selectively-etched second insulating layer as a mask pattern; and

forming a new wiring layer on said second insulating layer after selectively etching said first insulating layer.

REMARKS

As discussed with the Examiner, this Amendment corrects an obvious typographical error in the previous Amendment which omitted several words from Claim

4. Entry of this Amendment prior to further examination is respectfully solicited.

Please grant any extensions of time required to enter this response and charge any additional required fees to our deposit account 06-0916.

Respectfully submitted,

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Dated: April 29, 2002

By:

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Application Number: 09/658,861
Filing Date: September 8, 2000
Attorney Docket Number: 08038.0027

APPENDIX TO SUPPLEMENTAL AMENDMENT OF APRIL 29, 2002

Version with Markings to Show Changes Made

Amendment to Claim 4

4. (Twice Amended) A method of manufacturing a semiconductor device, said method comprising the steps of:

forming a wiring layer on a semiconductor substrate having an active region formed thereon;

forming a first insulating layer containing carbon on said wiring layer,
forming a second insulating layer comprising silicon, carbon and nitrogen on said
first insulating layer;

selectively etching said second insulating layer until the surface of said first insulating layer is partially exposed.

selectively etching said first insulating layer with plasma, using said selectively-etched second insulating layer as a mask pattern; and

forming a new wiring layer on said second insulating layer after selectively etching said first insulating layer.

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Subject: U.S. Appln. Serial No. 09/658,861

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